

Part f#7

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DCK
M122-1789SERIAL NO.
09/976,624LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)APPLICANT
Werner Juengling et al.FILING DATE
October 12, 2001GROUP
2813

U.S. PATENT DOCUMENTS

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA					
	AB					
	AC					
	AD					
	AE					
	AF					
	AG					
	AH					

FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Subclass	Translation	
					Yes	No
AI						

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

EK	AJ		M. Togo et al., "A Gate-side Air-gap Structure (GAS) to Reduce the Parasitic Capacitance in MOSFETs", 1996 Symposium on VLSI Technology Digest of Technical Papers, IEEE June 1996, pgs. 38-39.
EK	AK		Anand et al., "NURA: A Feasible, Gas-Dielectric Interconnect Process", 1996 Symposium on VLSI Technology Digest of Technical Papers, IEEE June 1996, pgs. 8283.
EK	AL		Watanabe et al., "A Novel Stacked Capacitor with Porous-Si Electrodes for High Density DRAMs", Symposium on VLSI Technology, Issue 1993, pg. 17, 1993. Year is sufficiently early so that the month is not an issue.
EK	AM		Townsend, et al., "Silk Polymer Coating with Low Dielectric Constant and High Thermal Stability for ULSI Interlayer Dielectric", Proceedings MRS, San Francisco, CA Vol. 476, April 1997, pgs. 9-17.
EK	AN		Product Brochure and Material Safety Data Sheet, "Interlayer Dielectric", JSR Microelectronics, 12 pages, June and July 1997.

EXAMINER

Eck Kai

DATE CONSIDERED

9/28/02

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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1789		SERIAL NO. 09/976,624				
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		FILING DATE October 12, 2001						
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
EK	AA	5,149,615	9/1992	Chakravorty et al.				
EK	AB	5,808,854	9/1998	Figura et al.				
EK	AC	5,559,666	9/1996	Figura et al.				
EK	AD	5,464,786	11/1995	Figura et al.				
EK	AE	5,654,224	8/1997	Figura et al.				
EK	AF	5,266,519	11/1993	Iwamoto				
EK	AG	5,970,360	10/1999	Cheng et al				
	AH							
	AI							
	AJ							
	AK							
	AL							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
EK	AM	EP 0 923 125 A	6/16/99	EP			✓	
EK	AN	EP 0 542 262 A	5/19/93	EP				
	AO							
	AP							
	AQ							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
EK	AR		"Monolithic Integration of 3-D Electroplated Microstructures with Unlimited Number of Levels Using Planarization with a Sacrificial Metallic Mold"; Yoon et al.; IEEE International Micro-Electro Mechanical Systems Conference; 1999; pps. 624 & 627-629.					
	AS							
	AT							
EXAMINER Eric Kirk				DATE CONSIDERED 9/28/02				
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